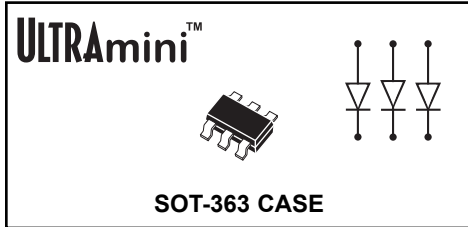


CMKSH2-4LR
SURFACE MOUNT
ULTRAmi™
TRIPLE ISOLATED
SILICON LOW V_F SCHOTTKY DIODES



Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKSH2-4LR type contains three (3) Isolated Silicon Low V_F Schottky Diodes, epoxy molded in a SOT-363 surface mount package. This ULTRAmi™ device has been designed for switching applications requiring a low forward voltage drop.

MARKING CODE: CHTL

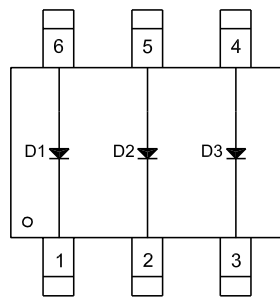
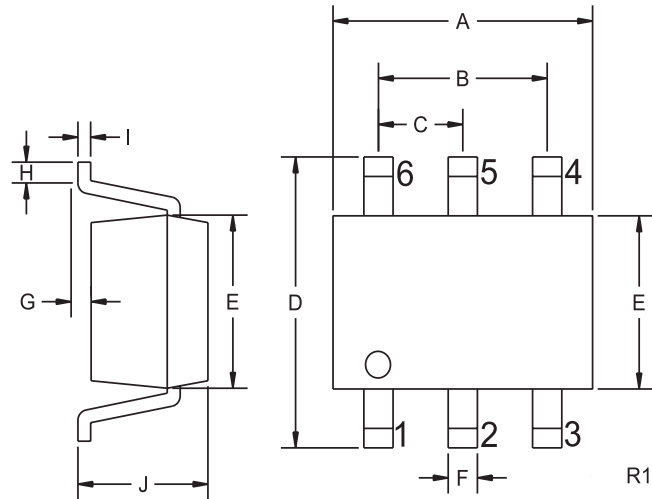
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	200	mA
Peak Repetitive Forward Current	I_{FRM}	350	mA
Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=20\text{V}$		11	50	μA
BV_R	$I_R=100\mu\text{A}$	40	53		V
V_F	$I_F=10\text{mA}$		0.24	0.325	V
V_F	$I_F=100\text{mA}$		0.35	0.4	V
V_F	$I_F=200\text{mA}$		0.42	0.5	V
C_T	$V_R=4.0\text{V}, f=1.0\text{ MHz}$		8.5	10	pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		4.0	5.0	ns

SOT-363 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

LEAD CODE:

- 1) CATHODE D1
- 2) CATHODE D2
- 3) CATHODE D3
- 4) ANODE D3
- 5) ANODE D2
- 6) ANODE D1

MARKING CODE: CHTL